**Product data sheet** 

# 1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a small SOT457 (SC-74) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

## 2. Features and benefits

- Trench MOSFET technology
- Low threshold voltage
- Enhanced power dissipation capability of 1400 mW

# 3. Applications

- · Relay driver
- High-speed line driver
- High-side loadswitch
- Switching circuits

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	-20	V
V <sub>GS</sub>	gate-source voltage			-12	-	12	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 25 °C; t ≤ 5 s	[1]	-	-	-6.8	Α
Static characte	Static characteristics						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = -4.5 V; $I_D$ = -5.2 A; $T_j$ = 25 °C		-	30	34	mΩ

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.



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# 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol	
1	D	drain	<u> </u>	D 	
2	D	drain			
3	G	gate	□ □ 1 □ 2 □ 3 TSOP6 (SOT457)	G T	
4	S	source		TSOP6 (SOT457)	\$ 017aaa257
5	D	drain			
6	D	drain			

# 6. Ordering information

Table 3. Ordering information

	Type number	Package				
		Name	Description	Version		
	PMN30XP	TSOP6	plastic surface-mounted package (TSOP6); 6 leads	SOT457		

# 7. Marking

Table 4. Marking codes

Type number	Marking code
PMN30XP	3A

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# 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-20	V
$V_{GS}$	gate-source voltage			-12	12	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 25 °C; t ≤ 5 s	[1]	-	-6.8	Α
		V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	-5.2	Α
		V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 100 °C	[1]	-	-3.3	Α
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \mu s$		-	-21	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	550	mW
			[1]	-	1.4	W
		T <sub>sp</sub> = 25 °C		-	6.25	W
Tj	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-drain	diode					
Is	source current	T <sub>amb</sub> = 25 °C	[1]	-	-1.3	Α

- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

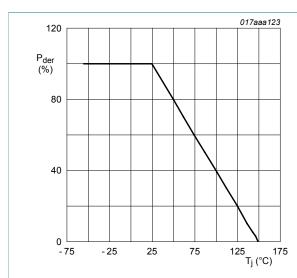


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

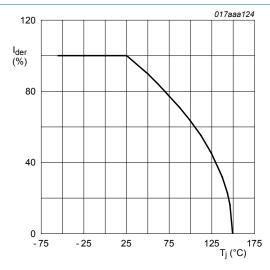


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

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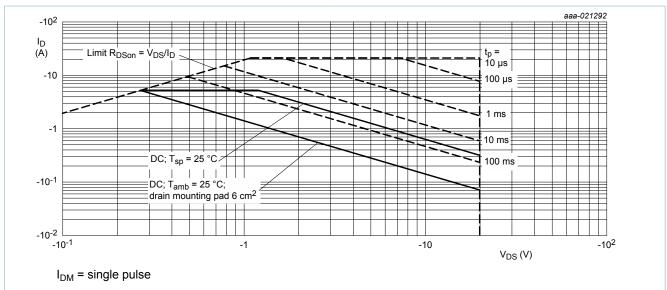


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drainsource voltage

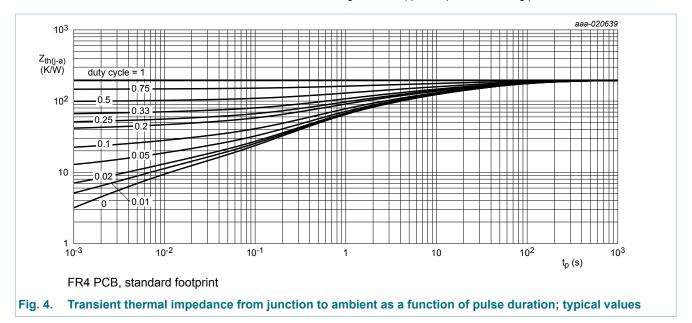
20 V, P-channel Trench MOSFET

## 9. Thermal characteristics

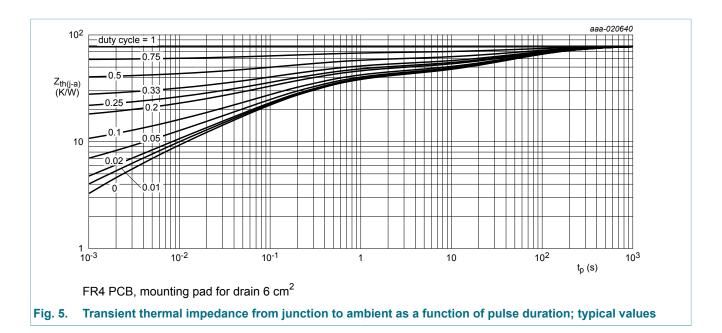
Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
ang a)	thermal resistance		[1]	-	195	225	K/W
	from junction to ambient		[2]	-	78	90	K/W
	ambient	in free air; t ≤ 5 s	<u>[2]</u>	-	45	52	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	15	20	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.



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# 10. Characteristics

#### Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics		'			
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = -250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	-20	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = -250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	-0.47	-0.68	-0.9	V
I <sub>DSS</sub>	drain leakage current	$V_{DS}$ = -20 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-	-	-1	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 12 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	100	nA
		V <sub>GS</sub> = -12 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-100	nA
R <sub>DSon</sub>	drain-source on-state	$V_{GS}$ = -4.5 V; $I_D$ = -5.2 A; $T_j$ = 25 °C	-	30	34	mΩ
	resistance	V <sub>GS</sub> = -4.5 V; I <sub>D</sub> = -5.2 A; T <sub>j</sub> = 150 °C	-	46	52	mΩ
		$V_{GS}$ = -2.5 V; $I_D$ = -4.6 A; $T_j$ = 25 °C	-	35	44	mΩ
		V <sub>GS</sub> = -1.8 V; I <sub>D</sub> = -1 A; T <sub>j</sub> = 25 °C	-	45	65	mΩ
		$V_{GS}$ = -1.5 V; $I_D$ = -0.1 A; $T_j$ = 25 °C	-	65	130	mΩ
9fs	forward transconductance	$V_{DS}$ = -10 V; $I_D$ = -5.3 A; $T_j$ = 25 °C	-	28	-	S
$R_G$	gate resistance	f = 1 MHz; T <sub>j</sub> = 25 °C	-	4.5	-	Ω
Dynamic c	haracteristics			'		
Q <sub>G(tot)</sub>	total gate charge	$V_{DS}$ = -10 V; $I_{D}$ = -5.5 A; $V_{GS}$ = -4.5 V;	-	15	23	nC
$Q_{GS}$	gate-source charge	T <sub>j</sub> = 25 °C	-	2	-	nC
$Q_{GD}$	gate-drain charge		-	4	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = -10 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	1575	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	145	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	125	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = -10 V; $I_{D}$ = -5.5 A; $V_{GS}$ = -4.5 V;	-	12	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	42	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	62	-	ns
t <sub>f</sub>	fall time		-	23	-	ns
Source-dra	ain diode		1	1	1	
$V_{SD}$	source-drain voltage	$I_S = -1.3 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-0.7	-1.2	V

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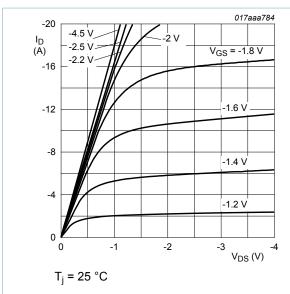


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

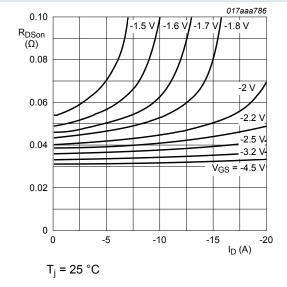


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

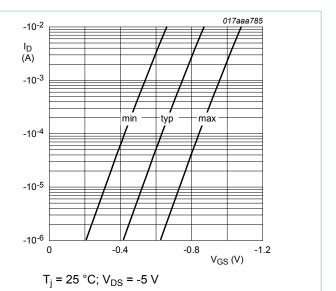


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

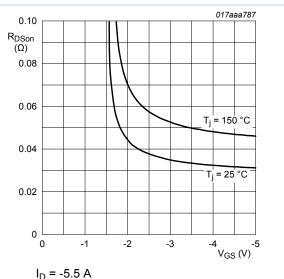
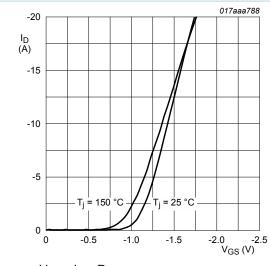


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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 $V_{DS} > I_D \times R_{DSon}$ 

Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

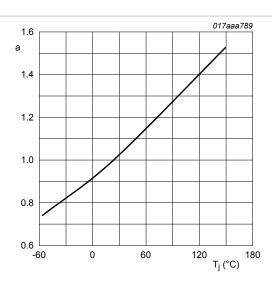
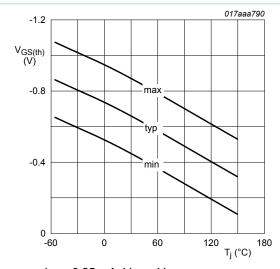


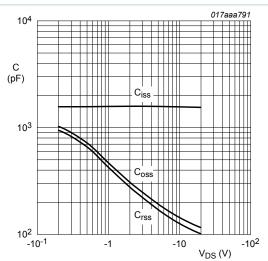
Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$



 $I_D$  = -0.25 mA;  $V_{DS}$  =  $V_{GS}$ 

Fig. 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$ 

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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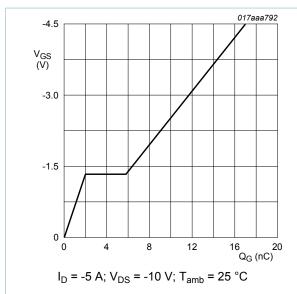


Fig. 14. Gate-source voltage as a function of gate charge; typical values

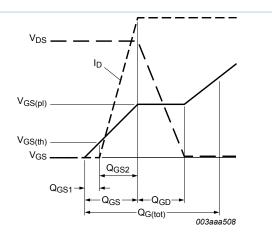


Fig. 15. MOSFET transistor: Gate charge waveform definitions

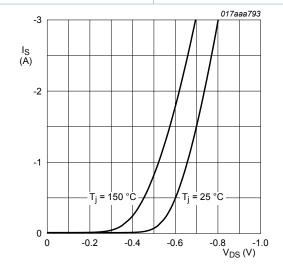
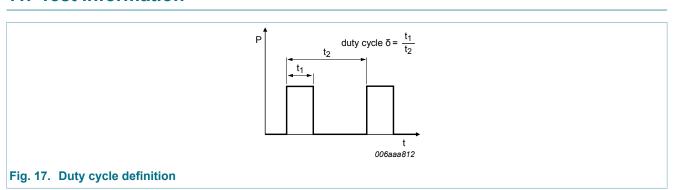


Fig. 16. Source current as a function of source-drain voltage; typical values

## 11. Test information

 $V_{GS} = 0 V$ 



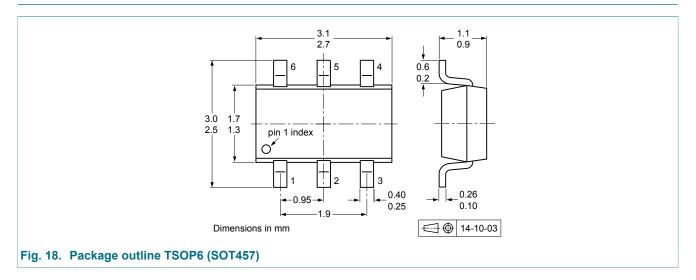
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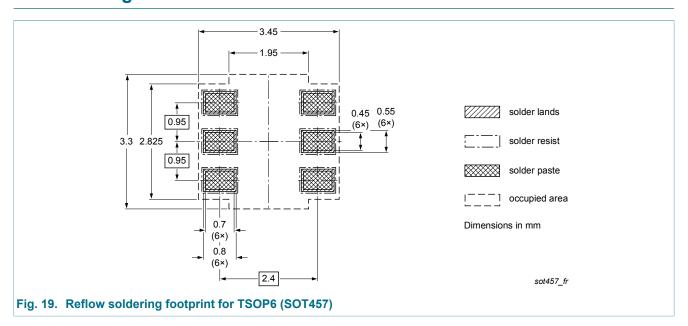
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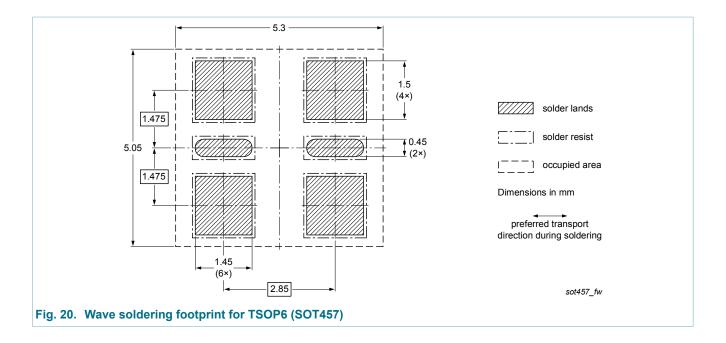
# 12. Package outline



# 13. Soldering



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# 14. Revision history

### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMN30XP v.1	20160223	Product data sheet	-	-

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#### 20 V, P-channel Trench MOSFET

## 15. Legal information

#### 15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
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Product [short] data sheet	Production	This document contains the product specification.

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